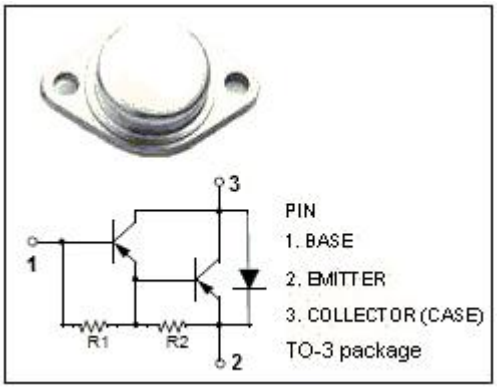
isc Silicon PNP Darlingtion Power Transistor 2N6286

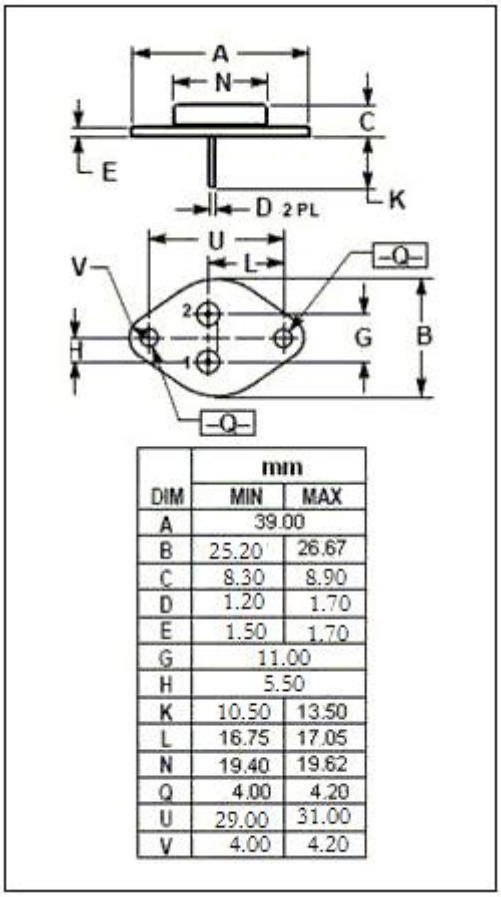
DESCRIPTION

- Built-in Base-Emitter Shunt Resistors
- High DC current gain-
  h_{FE} = 750 (Min) @ I_C = -10 Adc
- Collector-Emitter Sustaining Voltage-
  $V_{CEO(SUS)}$= -80V(Min)
- Complement to type 2N6283
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Intended for general purpose amplifier and low frequency switching applications, such as linear and switching industrial equipment.



DIM	mm MIN	MAX
A	39.00	
B	25.20	26.67
C	8.30	8.90
D	1.20	1.70
E	1.50	1.70
G	11.00	
H	5.50	
K	10.50	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	29.00	31.00
V	4.00	4.20

ABSOLUTE MAXIMUM RATINGS(T_C=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current -Continuous	-20	A
I_{CP}	Collector Current-Peak	-40	A
I_B	Base Current	-0.5	A
P_C	Collector Power Dissipation@T_C=25℃	160	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	ThermalResistance, Junction to Case	1.09	℃/W

isc Silicon PNP Darlington Power Transistor 2N6286

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -50mA ; I_B= 0	-80		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -10A; I_B= -40mA		-2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -20A; I_B= -200mA		-3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation voltage	I_C= -20A; I_B= -200mA		-4.0	V
$V_{BE(on)}$	Base-Emitter On voltage	I_C= -10A; V_{CE}= -3V		-2.8	V
I_{CEO}	Collector Cutoff current	V_{CE}= -40V; I_B=0		-1.0	mA
I_{EBO}	Emitter Cut-off current	V_{EB}= -5V; I_C= 0		-2.0	mA
h_{FE-1}	DC Current Gain	I_C= -10A; V_{CE}= -3V	750	18000	
h_{FE-2}	DC Current Gain	I_C= -20A; V_{CE}= -3V	100		
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V;f_{test}= 1.0MHz		600	pF